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INFORMAT	ION DISCLOSURE	Application Number	Unassigned	
STATEMEN	IT BY APPLICANT	Filing Date	02/05/2002	
Data Submitta	ed: February 5, 2002	First Named Inventor	Igor KOUZNETSOV et al.	
Date Submitte	d. February 5, 2002	Group Art Unit	Unassigned	
(use as many	sheets as necessary)	Examiner Name	Unassigned	
1	of 7	Attorney Docket Number	035905-0118	5

				U.S. PATENT DOCUMENTS	3	
Examiner	Cite	U.S. Patent Document		Name of Patentee or Applicant of	Date of Publication of	Pages, Columns, Lines Where Relevant
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	INFORMATI	ION DISCLO	SURE	Application Number	Unassigned	
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	Date Submitted: February 5, 2002		First Named Inventor	Igor KOUZNETSOV et al.		
			Group Art Unit	Unassigned		
(use as many sheets as necessary)		Examiner Name	Unassigned			
Sheet	2	of	7	Attorney Docket Number	035905-0118	

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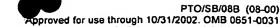
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	⊤8

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	INFORMATION DISCLOSURE			Application Number	Unassigned	
	STATEMEN	IT BY APPLI	CANT	Filing Date	02/05/2002	
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				Group Art Unit	Unassigned	
(use as many sheets as necessary)			cessary)	Examiner Name	Unassigned	
Sheet	3	of	7	Attorney Docket Number	035905-0118	

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Sheet	4	of	7	Attorney Docket Number	035905-0118	

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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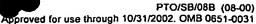
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	INFORMATION	DISCLO	SURE	Application Number	Unassigned
	STATEMENT BY	Y APPLI	CANT	Filing Date	02/05/2002
	Date Submitted: F	aha ian	5 2002	First Nam d Inventor	Igor KOUZNETSOV et al.
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	(use as many shee	ts as ne	cessary)	Examiner Name	Unassigned
Sheet	7	of	7	Attorney Docket Number	035905-0118

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